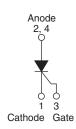


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Vishay Semiconductors

Thyristor, Surface Mount, Phase Control SCR, 16 A





TO-263AB (D²PAK)

PRODUCT SUMMARY							
Package	TO-263AB (D ² PAK)						
Diode variation	Single SCR						
I _{T(AV)}	16 A						
V_{DRM}/V_{RRM}	800 V, 1200 V						
V_{TM}	1.25 V						
I _{GT}	45 mA						
TJ	-40 to +125 °C						

FEATURES

- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Designed and qualified according JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





RoHS COMPLIANT **HALOGEN** FREE

APPLICATIONS

- Input rectification (soft start)
- · Vishay input diodes, switches and output rectifiers which are available in identical package outlines

DESCRIPTION

The VS-25TTS...SPbF High Voltage Series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS									
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS									
NEMA FR-4 or G10 glass fabric-based epoxy with 4 oz. (140 μm) copper	3.5	5.5							
Aluminum IMS, R _{thCA} = 15 °C/W	8.5	13.5	A						
Aluminum IMS with heatsink, R _{thCA} = 5 °C/W	16.5	25.0							

Note

T_A = 55 °C, T_J = 125 °C, footprint 300 mm²

MAJOR RATINGS	AND CHARACTERISTICS		
PARAMETER	TEST CONDITIONS	VALUES	UNITS
I _{T(AV)}	Sinusoidal waveform	16	۸
I _{RMS}		25	Α
V _{RRM} /V _{DRM}		800 to 1200	V
I _{TSM}		350	А
V _T	16 A, T _J = 25 °C	1.25	V
dV/dt		500	V/µs
dl/dt		150	A/µs
TJ		-40 to +125	°C

VOLTAGE RATINGS			
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} , AT 125 °C mA
VS-25TTS08SPbF	800	800	10
VS-25TTS12SPbF	1200	1200	10



ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEC	T CONDITIONS	VAL	UNITS		
PANAMETEN	STIMBUL	STMBOL TEST CONDITIONS			MAX.	UNITS	
Maximum average on-state current	I _{T(AV)}	T _C = 93 °C, 180° c	onduction half sine wave	1	6		
Maximum RMS on-state current	I _{RMS}			2	5	Α	
Maximum peak, one-cycle,	I	10 ms sine pulse,	rated V _{RRM} applied	3	00	^	
non-repetitive surge current	I _{TSM}	10 ms sine pulse,	no voltage reapplied	3	50		
Maximum I ² t for fusing	l ² t	10 ms sine pulse,	rated V _{RRM} applied	4	50	A ² s	
Waxiinum F Clor lusing	1 (10 ms sine pulse,	10 ms sine pulse, no voltage reapplied		30	A-5	
Maximum I ² √t for fusing	I²√t	t = 0.1 ms to 10 m	s, no voltage reapplied	6300		A²√s	
Maximum on-state voltage drop	V_{TM}	16 A, T _J = 25 °C		1.25		V	
On-state slope resistance	r _t	T 405.00		12	2.0	mΩ	
Threshold voltage	V _{T(TO)}	$T_{J} = 125 ^{\circ}\text{C}$ 1.0		.0	V		
Maximum reverse and direct leakage current	1/1	T _J = 25 °C	V Pated V	0	.5		
Maximum reverse and direct leakage current	'RM' 'DM	I_{RM}/I_{DM} $V_R = Rated V_{RRM}/V_{DRM}$ 10		0			
Holding current	I _H	VS-25TTS08, VS-25TTS12 Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C		i	150	mA	
Maximum latching current	ΙL	Anode supply = 6 V, resistive load, T _J = 25 °C		200			
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J$ max., linear to 80 %, $V_{DRM} = R_g - k = Open$., linear to 80 %, $V_{DRM} = R_g - k = Open$		V/µs	
Maximum rate of rise of turned-on current	dl/dt			1:	50	A/µs	

TRIGGERING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum peak gate power	P _{GM}		8.0	W			
Maximum average gate power	P _{G(AV)}		2.0	VV			
Maximum peak positive gate current	+ I _{GM}		1.5	Α			
Maximum peak negative gate voltage	- V _{GM}		10	V			
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, T _J = - 10 °C	60	1			
	I _{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	45	mA			
		Anode supply = 6 V, resistive load, T _J = 125 °C	20				
		Anode supply = 6 V, resistive load, T _J = - 10 °C	2.5				
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	2.0	1			
		Anode supply = 6 V, resistive load, T _J = 125 °C	1.0	V			
Maximum DC gate voltage not to trigger	V_{GD}	T 105 °C V Detectively	0.25				
Maximum DC gate current not to trigger	I _{GD}	T _J = 125 °C, V _{DRM} = Rated value	2.0	mA			

SWITCHING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9				
Typical reverse recovery time	t _{rr}	T _{.I} = 125 °C	4	μs			
Typical turn-off time	t _q	1J = 125	110				

THERMAL AND MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum junction and storage temperature range	T _J , T _{Stg}		-40 to +125	°C				
Soldering temperature	T _S	For 10 s (1.6 mm from case)	260					
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	1.1	°C/W				
Typical thermal resistance, junction to ambient (PCB mount)	R _{thJA} ⁽¹⁾		40	O/VV				
Approximate weight			2	g				
Approximate weight			0.07	OZ.				
Marking daving		Case style D ² PAK (SMD-220)	25TTS08S					
Marking device		Case style D-PAN (SIVID-220)	25TTS12S					

Note

⁽¹⁾ When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 µm] copper 40 °C/W For recommended footprint and soldering techniques refer to application note #AN-994

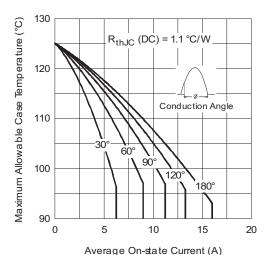
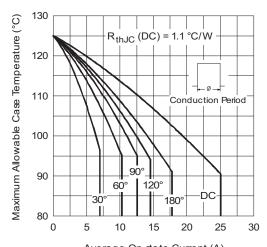


Fig. 1 - Current Rating Characteristics



Average On-state Current (A) Fig. 2 - Current Rating Characteristics

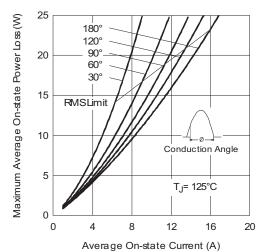
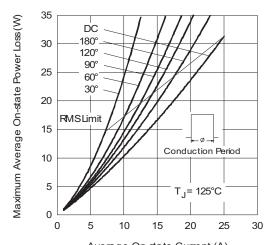


Fig. 3 - On-State Power Loss Characteristics



Average On-state Current (A)
Fig. 4 - On-State Power Loss Characteristics

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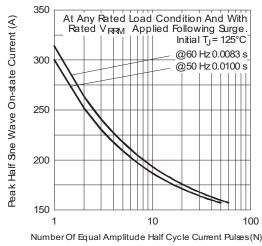


Fig. 5 - Maximum Non-Repetitive Surge Current

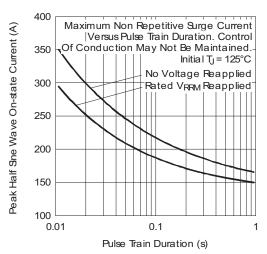


Fig. 6 - Maximum Non-Repetitive Surge Current

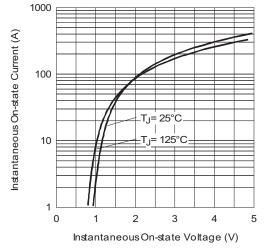


Fig. 7 - On-State Voltage Drop Characteristics

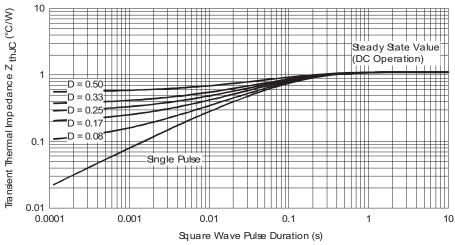


Fig. 8 - Gate Characteristics

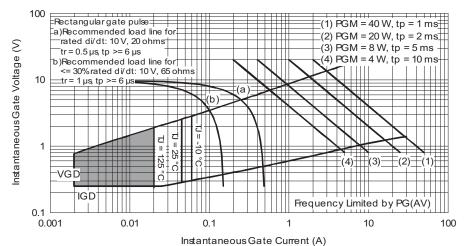
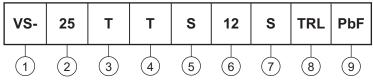


Fig. 9 - Thermal Impedance Z_{thJC} Characteristics

ORDERING INFORMATION TABLE

Dev		



- Vishay Semiconductors product
- Current rating (25 = 25 A)
- Circuit configuration:
 - T = single thyristor
- Package: T = TO-220AC
- 5 Type of silicon:
 - S = standard recovery rectifier
- 08 = 800 V6 Voltage rating: voltage code x 100 = V_{RRM} 12 = 1200 V
- 7 S = TO-220 D²PAK (SMD-220) version
- None = tube
 - TRL = tape and reel (left oriented)
 - TRR = tape and reel (right oriented)
- 9 PbF = lead (Pb)-free

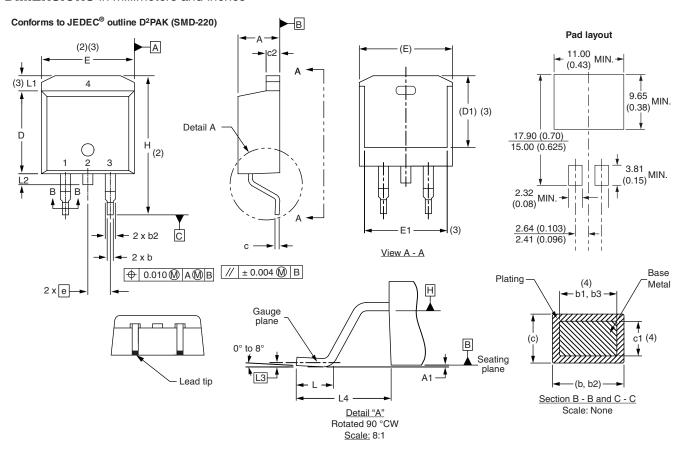
ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-25TTS08SPbF	50	1000	Antistatic plastic tubes					
VS-25TTS08STRRPbF	800	800	13" diameter reel					
VS-25TTS08STRLPbF	800	800	13" diameter reel					
VS-25TTS12SPbF	50	1000	Antistatic plastic tubes					
VS-25TTS12STRRPbF	800	800	13" diameter reel					
VS-25TTS12STRLPbF	800	800	13" diameter reel					

LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95046</u>					
Part marking information	www.vishay.com/doc?95054				
Packaging information	www.vishay.com/doc?95032				



D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIM	ETERS	INC	HES	NOTES	
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES		STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC® outline TO-263AB



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